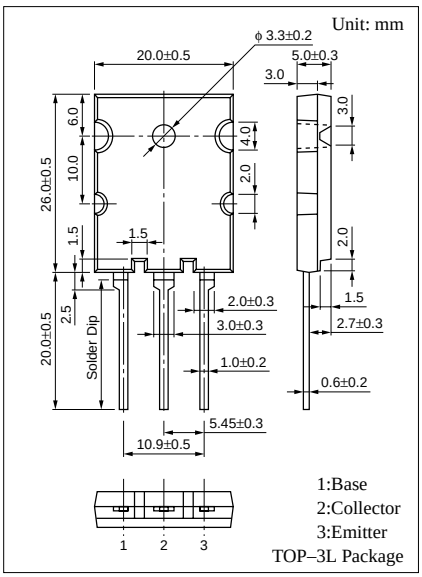
2SB1502

Silicon PNP epitaxial planar type Darlington

For power amplification
Complementary to 2SD2275



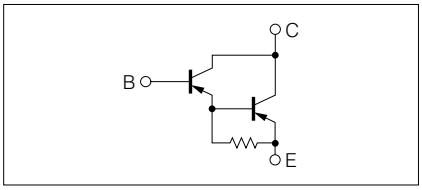
Features

- Optimum for 55W HiFi output
- High foward current transfer ratio h_{FE}: 5000 to 30000
- Low collector to emitter saturation voltage $V_{CE(sat)}$: < 2.5V

Absolute Maximum Ratings (T_C=25˚C)

Parameter		Symbol	Ratings	Unit
Collector to base voltage		V_{CBO}	–120	V
Collector to emitter voltage		V_{CEO}	–100	V
Emitter to base voltage		V_{EBO}	–5	V
Peak collector current		I_{CP}	–8	A
Collector current		I_C	–5	A
Collector power dissipation	T_C=25°C	P_C	60	W
	Ta=25°C		3.5	
Junction temperature		T_j	150	˚C
Storage temperature		T_{stg}	–55 to +150	˚C

Internal Connection



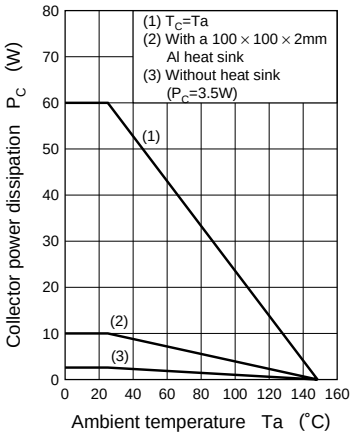
Electrical Characteristics (T_C=25˚C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = –120V, I_E = 0			–100	µA
	I_{CEO}	V_{CE} = –100V, I_B = 0			–100	µA
Emitter cutoff current	I_{EBO}	V_{EB} = –5V, I_C = 0			–100	µA
Collector to emitter voltage	V_{CEO}	I_C = –30mA, I_B = 0	–100			V
Forward current transfer ratio	h_{FE1}	V_{CE} = –5V, I_C = –1A	2000			
	h_{FE2}*	V_{CE} = –5V, I_C = –4A	5000		30000	
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = –4A, I_B = –4mA			–2.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	I_C = –4A, I_B = –4mA			–3.0	V
Transition frequency	f_T	V_{CE} = –10V, I_C = – 0.5A, f = 1MHz		20		MHz
Turn-on time	t_{on}	I_C = –4A, I_{B1} = –4mA, I_{B2} = 4mA, V_{CC} = –50V		1.0		µs
Storage time	t_{stg}			0.8		µs
Fall time	t_f			1.0		µs

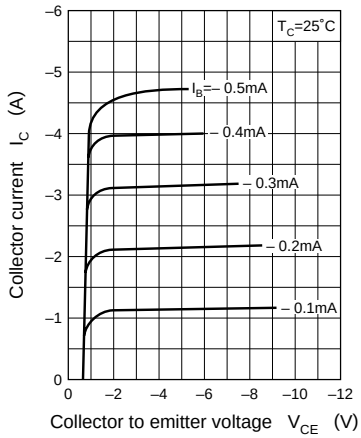
*h_{FE2} Rank classification

Rank	Q	S	P
h_{FE2}	5000 to 15000	7000 to 21000	8000 to 30000

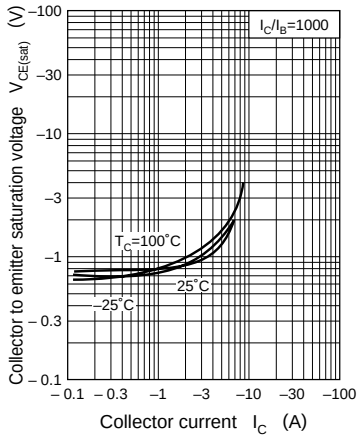
P_C — Ta



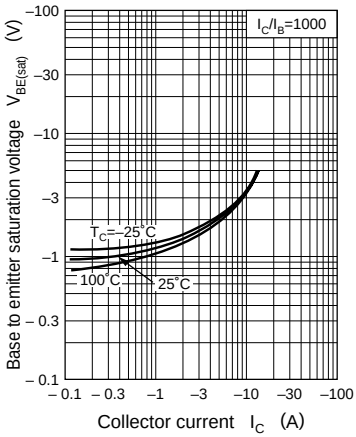
I_C — V_{CE}



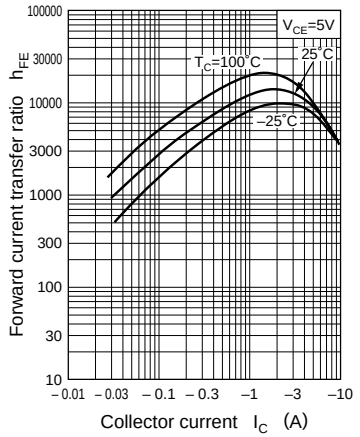
$V_{CE(sat)}$ — I_C



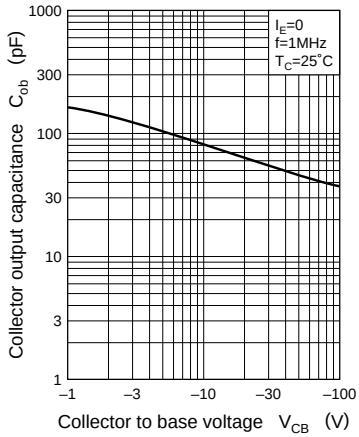
$V_{BE(sat)}$ — I_C



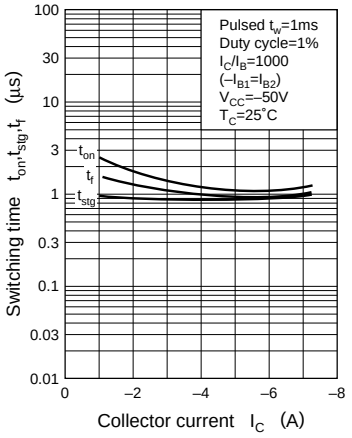
h_{FE} — I_C



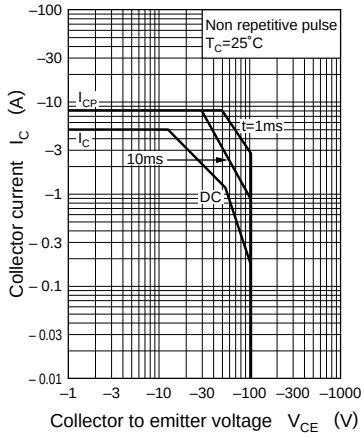
C_{ob} — V_{CB}



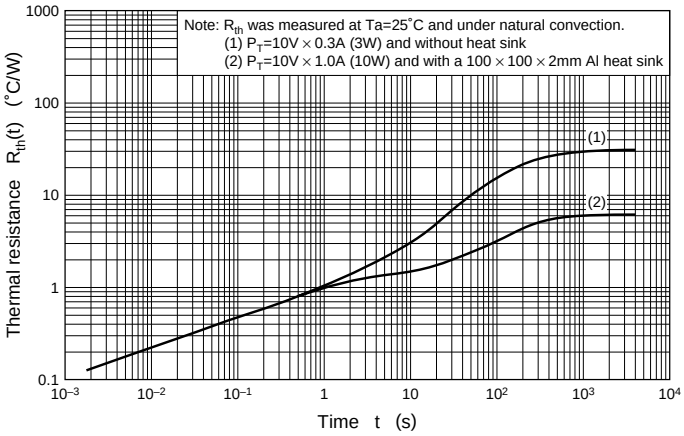
t_{on}, t_{stg}, t_f — I_C



Area of safe operation (ASO)



$R_{th(t)}$ — t


Note: R_{th} was measured at Ta=25°C and under natural convection.
(1) P_T=10V × 0.3A (3W) and without heat sink
(2) P_T=10V × 1.0A (10W) and with a 100 × 100 × 2mm Al heat sink
Thermal resistance $R_{th}(t)$ (°C/W)
1000
100
10
1
0.1
(1)
(2)
10^{-3}
10^{-2}
10^{-1}
1
10
10^{2}
10^{3}
10^{4}
Time t (s)